

A STACKED MAGNETIC MEMORY STRUCTURE**Abstract**

The invention includes a stacked magnetic memory structure. The magnetic memory structure includes a stacked magnetic memory structure. The first layer includes a first plurality of magnetic tunnel junctions. A second layer is formed adjacent to the first layer. The second layer includes a second plurality of magnetic tunnel junctions. The stacked magnetic memory structure further includes a common first group conductor connected to each of the first plurality of magnetic tunnel junctions and the second plurality of magnetic tunnel junctions.